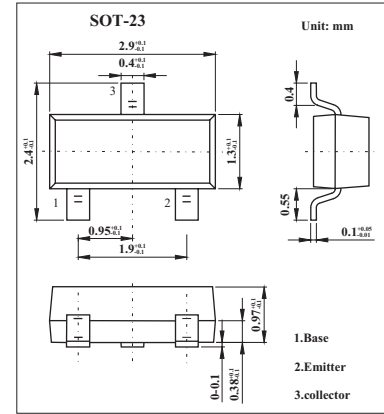


Medium Power Transistor

FMMT591

■ Features

- Low equivalent on-resistance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-80	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EBO}	-5	V
Peak collector current	I _{CM}	-2	A
Collector current	I _C	-1	A
Base current	I _B	-200	mA
Power dissipation	P _{tot}	500	mW
Operating and storage temperature range	T _J , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA	-80			V
Collector-emitter breakdown voltage *	V _{(BR)CEO}	I _C =-10mA	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA	-5			V
Collector cutoff current	I _{CBO}	V _{CB} =-60V			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V			-100	nA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =-1A, I _B =-100mA			-0.6	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =-1A, I _B =-100mA			-1.2	V
Base-emitter voltage *	V _{BE(ON)}	I _C =-1A, V _{CE} =-5V			-1.0	V
Static Forward Current TransferRatio	h _{FE}	I _C =-1mA, V _{CE} =-2V*	100			
		I _C =-500mA, V _{CE} =-5V	100		300	
		I _C =-1A, V _{CE} =-2V*	80			
		I _C =-2A, V _{CE} =-2V*	40			
Current-gain-bandwidth product	f _T	I _C =-50mA, V _{CE} =-10V, f=100MHz	150			MHz
Output capacitance	C _{obo}	V _{CB} =-10V, f=1MHz			10	pF

* Pulse test: t_p ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	591
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